Optical Detection of a Single Nuclear Spin

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We propose a method to optically detect the spin state of a ^{31}P nucleus embedded in a ^{28}Si matrix. The nuclear-electron hyperfine splitting of the ^{31}P neutral-donor ground state can be resolved via a direct frequency discrimination measurement of the ^{31}P-bound exciton photoluminescence using single photon detectors. The measurement time is expected to be shorter than the lifetime of the nuclear spin at 4 K and 10 T.

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The spin qubit embedded in a crystalline host is an attractive choice for solid-state quantum computation due to its long coherence time. The inevitable cost of the spin qubit's isolation from the environment is the difficulty of measuring its quantum state. Scanning tunnelling microscopy and single molecule spectroscopy have pushed close to this limit by reporting single nuclear and single electron spin resonances [1, 2, 3], yet measurement of the quantum state of a single spin in the solid state remains elusive.

Nuclei in semiconductors, in particular silicon, have generated particular interest for solid-state quantum computation. The proposal of Kane [4, 5], in which qubits are encoded as the spin state of single embedded ^{31}P nuclei, proposes to solve the single nuclear measurement problem by adiabatically transferring the nuclear state to the spin of the electron bound to the ^{31}P impurity and measuring the electron's spin-correlated charge state with a single electron transistor (SET). In practice, however, charge fluctuations produced by the SET couple back to the ^{31}P nucleus via the electron's strong hyperfine interaction, leading to a decoherence source that is not present in bulk silicon. Magnetic resonance force microscopy has approached single-electron-spin sensitivity, but experimental results thus far have shown that this probe induces spin relaxation more quickly than the needed measurement time [6], casting doubts on proposals that seek its use for quantum computation [7]. The use of ensembles of ^{29}Si nuclei in bulk silicon with no metallic gates has been proposed [8], but this scheme replaces the measurement problem with the challenge of achieving high nuclear polarization in order to maintain scalability. In this Letter, we propose an all-optical method to determine the nuclear spin state of an isolated ^{31}P impurity in bulk silicon. This method's incorporation into silicon-based quantum computation architectures could ease these difficulties.

In semiconductors, free excitons can be bound to donor and acceptor impurity sites, forming bound excitons. When a bound exciton (BE) decays radiatively to a neutral impurity state, its linewidth is characteristically narrow due to the localization of the exciton [9]. If the hyperfine interaction between the impurity nucleus and either the neutral impurity bound carrier or the impurity BE is sufficiently strong, the nuclear state of the impurity can be determined via the BE photoluminescence (PL) energy. The particular case of the ^{31}P donor in a ^{28}Si matrix is treated below.

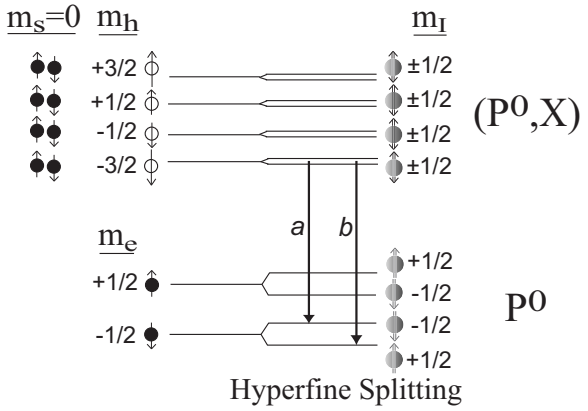


FIG. 1: Energy diagram for the neutral donor (P^0) and its bound exciton (P^0,X) in a magnetic field. The (P^0,X) state is populated via capture of a resonantly excited free exciton. The ^{31}P nuclear state can be determined by the energy difference of a and b.

In a magnetic field, the ground state of the ^{31}P BE, notated (P^0,X), is split into four hole Zéeman levels. The ground state of the neutral donor, P^0, is split into two electron Zéeman levels [10]. These levels are illustrated in Fig. 1. We assume a large applied magnetic field such that the electron/hole Zéeman interaction is much greater than the hyperfine interaction.

The P^0 state is described by effective mass theory (EMT), where the total wavefunction $\psi_{\rm e}(\mathbf{r})$ of the donor electron is given by the product of the EMT envelope function $F(\mathbf{r})$ and the Bloch wavefunction $\varphi(\mathbf{r}) = u(\mathbf{r})e^{i\mathbf{k}\cdot\mathbf{r}}$. Both the Bloch and envelope functions are s-like, so the dominant part of the hyperfine interaction is the Fermi contact term [11],

$$\mathcal{H}_{\rm C} = -\frac{\mu_0}{4\pi} g_0 \mu_{\rm B} \hbar \gamma_{\rm n} \frac{8\pi}{3} \mathbf{I}\cdot\mathbf{S}\ \delta(\mathbf{r}), \qquad (1)$$

where g_0 is the free-electron g-factor, γ_n is the ^{31}P gyromagnetic ratio, $\mathbf{I}$ is the nuclear spin operator, and $\mathbf{S}$ is the electron spin operator. When an exciton is bound to the neutral-donor site, the two electrons form an antisymmetric spin singlet state [15, 16]. Consequently, the hyperfine splitting of the BE is determined only by the spin of the bound hole. Since the hole Bloch function is p-like, the Fermi contact term is negligible, and assuming that the envelope function is s-like, the orbital and dipolar terms will be much smaller than the P^0 contact hyperfine splitting. Thus, the energy difference between the transitions a and b of the (P^0,X) PL, shown in Fig. 1, is determined entirely by the hyperfine splitting of the P^0 state. From Eq. (1), this splitting is

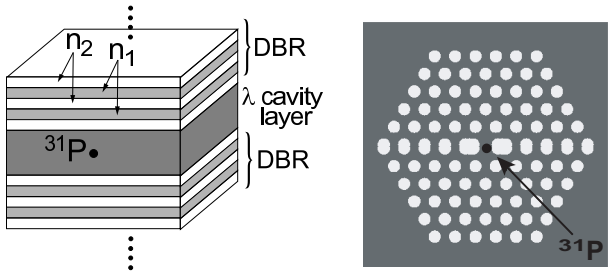
$$\Delta E_{\mathrm{HF,P^0}} = \frac{\mu_0}{3} g_0 \mu_B \gamma_n \hbar |\psi_e(0)|^2. \quad (2)$$

The electron density at the ^{31}P ($\mathbf{r} = 0$) site has been determined via electron spin resonance to be 0.44×10^{24} cm^{-3}, corresponding to a $\Delta E_{\mathrm{HF,P^0}}$ of 60 MHz [12]. This splitting has also been calculated with reasonable accuracy using a corrected envelope function to account for the discrepancy in the observed and EMT ionization energies [13, 14].

The (P^0,X) state in Si decays primarily via a nonradiative Auger process with a lifetime of 300 ns [18]. However, there exists a zero-phonon radiative channel with a lifetime of 2 ms [18]. The PL linewidth of a single ^{31}P donor impurity is thus expected to be approximately 3 MHz, which is much smaller than the hyperfine splitting of 60 MHz. Experimentally, the PL linewidth from an ensemble of ^{31}P impurities was measured to be less than 150 MHz at 2 K, which includes an inhomogeneous broadening effect and was limited by the spectrometer resolution [9].

After Auger recombination, the electron/hole recombination energy is imparted to the second electron, which is ionized. To ensure a fast recapture process of the donor electron, one can optically excite conduction electrons. Simultaneously, one can resonantly excite free excitons which will be captured at the neutral-donor site. The BE will relax thermally within its lifetime [10], and in a magnetic field of 10 T at 4 K, the probability for it to occupy the lowest Zéeman level is 0.8. Thus, approximately 400 photons/s are emitted at the desired transitions a and b in Fig. 1.

The extraction of an emitted photon out of the high-refractive-index Si substrate as a well-collimated beam for optical detection is not trivial. For this purpose, one can incorporate a planar distributed Bragg reflector (DBR) cavity, as shown in Fig. 2(a), at the center of which a ^{31}P impurity is embedded. The cavity modifies the radiation pattern and concentrates the emitted power in the normal direction. With high and low DBR refractive indices $n_1 = 3.0$ and $n_2 = 1.5$, the output coupling efficiency (β-factor) into a beam emitted in a normal direction can be as high as 0.8 for a random dipole orientation [20]. This efficiency is achieved at the cost of a decreased radiative decay rate by a factor of 3 [20]. The overall number of PL photons available for optical detection would then be $400 \times 0.8/3 \sim 100$ photons/s.



(a) (b)

FIG. 2: (a) DBR planar cavity including a ^{31}P impurity at the center of the one-wavelength-thick optical cavity layer. (b) 2D photonic crystal structure including a ^{31}P impurity at the central defect [19].

Alternatively, a two-dimensional photonic crystal structure (Fig. 2b) can simultaneously enhance the output coupling efficiency and the radiative decay rate. A detailed analysis based on the finite difference time domain (FDTD) method predicts that an optical mode volume of $0.5(\lambda/n)^3$, a Q value of 30,000, a spontaneous emission decay rate enhancement (Purcell) factor of 100, and a β-factor of 1 can be achieved [19]. The expected photon flux in this case is 4×10^4 photons/s.

In order to find the measurement time needed to determine the nuclear spin state, we calculate the signal-to-noise ratio for direct frequency detection. In the scheme illustrated by Fig. 3, the BE PL is collected and sent to input a of a Mach-Zender interferometer. The signal is split by the first beamsplitter into arms c and d, which have a phase difference of $\omega\tau$. Arms c and d are recombined at the second beamsplitter, and the photons in outputs e and f are detected by single photon detectors. The photocurrents are then subtracted, and the resulting current is time-integrated.

Assuming an input state with mean frequency ω_0 and a Lorentzian spectral lineshape with full-width-half-max γ, the average integrated single-photon current is proportional to

$$\langle I \rangle = e^{-\gamma\tau/2} \cos(\omega_0 \tau). \quad (3)$$

The variance of the current is proportional to

$$\langle \Delta I^2 \rangle = \langle I^2 \rangle - \langle I \rangle^2 = 1 - e^{-\gamma\tau} \cos^2(\omega_0 \tau). \quad (4)$$

The two input frequencies of the BE PL, corresponding to the two nuclear spin states, are centered around a mean frequency ω_0; we notate these frequencies $\omega_\pm =$

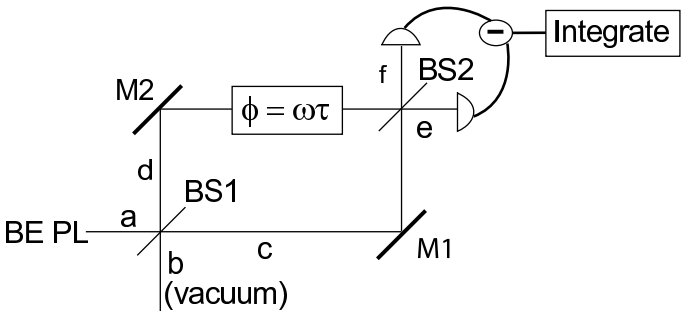


FIG. 3: Mach-Zender interferometer for frequency discrimination of BE PL.

$\omega_0 \pm \Delta\omega/2$, where $\hbar\Delta\omega = \Delta E_{\mathrm{HF,P^0}}$. The difference in the integrated current between the nuclear states is the signal, so the power signal-to-noise ratio per photon for such a frequency detection scheme is given by

$$\frac{S}{N} = \frac{\left[\sin\left(\frac{1}{2}\Delta\omega\tau\right) - \sin\left(-\frac{1}{2}\Delta\omega\tau\right)\right]^2}{\cos^2\left(\frac{1}{2}\Delta\omega\tau\right) + e^{\gamma\tau} - 1}, \qquad (5)$$

in which the interferometer is biased such that $\omega_0\tau = (m+\frac{1}{2})\pi$. The maximum signal-to-noise ratio is 0.084 per photon, assuming the upper bound on the PL linewidth of 150 MHz and a delay time $\tau = 2$ ns. Assuming 100 photons per second are collected, the minimum integration time needed for a signal-to-noise ratio of unity is approximately 0.1 s. If we assume an enhanced spontaneous emission decay rate with a 2D photonic structure mentioned above and a collection efficiency of 0.5, the minimum integration time is reduced to approximately 10^{-3} s.

Any practical detection scheme will suffer from detector efficiency and dark count rates. However, negligible dark count rates and a detection efficiency of 0.4 can be obtained at 1.1 μm with a superconducting transition edge sensor (TES) [21]. The effect of finite detector efficiency η_{d} is to decrease the signal-to-noise ratio by η_{d}, extending the measurement time.

Sufficient integration of the luminescence signal measures the nuclear spin state only if that state is stable over a sufficient number of excitation/luminescence cycles. Previous experiments measuring the resonance of single nuclei have shown only distributions over the nuclear states, as in a high-temperature ensemble, due to the randomization of the nuclear spins during the integration time of the measurement [3]. However, in the case of ^{31}P nuclei in silicon, it is known from ESR experiments that the equilibrium nuclear spin relaxation time T_1 of isolated ^{31}P nuclei exceeds 10 hours at 1.25 K and 0.8 T [22]. Such a long T_1 of solid-state nuclei is a combined consequence of the small number of nuclear interactions and a small density of states to which the nuclear Zéeman energy may be transferred. Cross relaxation with the phosphorous-bound electron, induced by the hyperfine interaction with the emission of a phonon, is also a slow process. It was measured to be 5 hours at 1.25 K and 0.8 T and should theoretically scale to 30 seconds at 4 K and 10 T [22]. Since the P^0 ground state only lasts nanoseconds before each optical re-excitation in this scheme, these already long equilibrium relaxation times are negligible. The nucleus may only be appreciably destabilized by the rapid optical excitations we introduce.

We first argue that nuclear spin relaxation due to optically excited, delocalized conduction electrons is not expected to be a significant effect. The number of conduction electrons required for neutralization of the Auger-ionized donors in 1 ns is approximately 10^{13} cm^{-3}, assuming a 4 K electron capture cross section of 4×10^{-11} cm^2 [23]. At this temperature, electrons are expected to thermalize quickly, in which case the T_1 theory described in Ref. [11] is applicable. This theory predicts a T_1 greater than 10^6 seconds. Even ^{29}Si in heavily doped ($> 10^{17}$ donors/cm^3) silicon has a measured T_1 in excess of 200 minutes at 4 K [24, 25]; the T_1 corresponding to ^{31}P nuclei would only be shorter by a factor of $\gamma^2_{^{29}\mathrm{Si}}/\gamma^2_{^{31}\mathrm{P}} = 4$, still leaving this timescale unimportant. An argument that T_1 due to free excitons should also be negligibly long follows a similar reasoning, since only the spin of the s-like electron interacts appreciably with the nucleus, and Boltzmann statistics may still be assumed.

Of greater concern is the probability of a nuclear spin flip during the capture of a free electron following the Auger process. Such a nuclear flip arises in second order perturbation theory, in which a virtual electron capture and a virtual electron/nuclear spin flip-flop in the neutral-donor state occur concurrently with the energy compensated by the real emitted phonon. To estimate the probability of such an event, we note that the energy cost of a hyperfine-induced electron/nuclear spin flip-flop (approximately the 1.2 meV Zéeman energy of the neutral-donor spin) is substantially smaller than the donor binding energy (45 meV). We may therefore assume that the density-of-states factors in Fermi's Golden Rule are unchanged between the first and second order processes, and that they are independent of the initial spin state. We also assume that the optical excitation of free carriers is not spin selective, and since T_1 for these carriers exceeds the capture time, this implies that the initial spin polarizations are approximately equal. It follows from these assumptions that the probability ratio between the first and second order processes is well approximated by the ratio between their matrix elements. The second order matrix element for an electron/nuclear flip-flop process, assuming without loss of generality that the nucleus begins in the $|\Downarrow\rangle$ state, may be written as

$$\left|V^{(2)}_{\mathrm{P^+}\uparrow\Downarrow\rightarrow\mathrm{P^0}\downarrow\Uparrow}\right|^2 = \left|\frac{\left\langle \mathrm{P^+}\uparrow\Downarrow\right| \mathcal{H}_{\mathrm{N}} \left|\mathrm{P^0}\uparrow\Downarrow\right\rangle \left\langle \mathrm{P^0}\uparrow\Downarrow\right| \mathcal{H}_{\mathrm{C}} \left|\mathrm{P^0}\downarrow\Uparrow\right\rangle}{E_{\mathrm{P^0}\downarrow\Uparrow} - E_{\mathrm{P^0}\uparrow\Downarrow}}\right|^2, \qquad (6)$$

in which $\left|\mathrm{P}^{+}\uparrow\Downarrow\right\rangle$ describes the ionized donor and $\left|\mathrm{P}^{0}\uparrow\Downarrow\right\rangle$ describes the neutral donor with electron spin up and nucleus spin down. These states are the only important ones for nuclear destabilization, since the $\left|\mathrm{P}^{0}\downarrow\Downarrow\right\rangle$ state is unperturbed by $\mathcal{H}_{\mathrm{C}}$. The unperturbed eigenenergy difference between the intermediate and final state, $E_{\mathrm{P}^0\downarrow\Uparrow} - E_{\mathrm{P}^0\uparrow\Downarrow}$, is a sum of the electron Zéeman term, the nuclear Zéeman term, and $\Delta E_{\mathrm{HF,P}^0}$; the electron Zéeman term dominates this sum. The Hamiltonian term $\mathcal{H}_{\mathrm{N}}$ refers to the interaction leading to the capture of the free electron; thus, a first-order matrix element for a neutralization process without a flip-flop is written as

$$\left|V^{(1)}_{\mathrm{P}^+\uparrow\Downarrow\rightarrow\mathrm{P}^0\uparrow\Downarrow}\right|^2 = \left|\left\langle \mathrm{P}^{+}\uparrow\Downarrow\right| \mathcal{H}_{\mathrm{N}} \left|\mathrm{P}^{0}\uparrow\Downarrow\right\rangle\right|^2 . \qquad (7)$$

We assume that this Coulombic process has no spin selectivity. It follows that the probability per transition of a flip-flop may be written as

$$\frac{\left|V^{(2)}_{\mathrm{P}^+\uparrow\Downarrow\rightarrow\mathrm{P}^0\downarrow\Uparrow}\right|^2}{\left|V^{(1)}_{\mathrm{P}^+\uparrow\Downarrow\rightarrow\mathrm{P}^0\uparrow\Downarrow}\right|^2 + \left|V^{(1)}_{\mathrm{P}^+\downarrow\Downarrow\rightarrow\mathrm{P}^0\downarrow\Downarrow}\right|^2 + \left|V^{(2)}_{\mathrm{P}^+\uparrow\Downarrow\rightarrow\mathrm{P}^0\downarrow\Uparrow}\right|^2} \approx \frac{1}{2}\left|\frac{\left\langle \mathrm{P}^{0}\uparrow\Downarrow\right| \mathcal{H}_{\mathrm{C}} \left|\mathrm{P}^{0}\downarrow\Uparrow\right\rangle}{E_{\mathrm{P}^0\downarrow\Uparrow} - E_{\mathrm{P}^0\uparrow\Downarrow}}\right|^2 = \frac{1}{2}\left(\frac{\Delta E_{\mathrm{HF,P}^0}}{g\mu_{\mathrm{B}}B_0}\right)^2 . \qquad (8)$$

This probability can be seen from an alternative viewpoint: if we use second-order time-independent perturbation theory to calculate the mixing of the $\left|\mathrm{P}^{0}\uparrow\Downarrow\right\rangle$ and $\left|\mathrm{P}^{0}\downarrow\Uparrow\right\rangle$ states due to the flip-flop terms of $\mathcal{H}_{\mathrm{C}}$, and presume that capture rates to these perturbed states are the same as to the unperturbed states, the same probability is obtained.

The free exciton capture process leads to a similar second-order probability for nuclear randomization. In this case, however, the binding energy of the free exciton to the neutral donor is only somewhat larger than the electron Zéeman energy, so the density-of-states factors in the transition rates can become important. However, we do not expect this correction to alter the per-transition probability by more than a factor of order unity. We thus estimate that at 10 T, the probability of a nuclear flip for each free-exciton-capture and free-electron-capture process is approximately twice the result of Eq. (8): $(60\ \mathrm{MHz}/280\ \mathrm{GHz})^2 = 5\times10^{-8}$. The consequences of this probability will be discussed shortly.

A nuclear spin flip can also occur in a similar manner during a free exciton capture or BE Auger decay due to the BE (hole/nuclear) hyperfine interaction. This process is less important because the BE hyperfine interaction is much weaker. The magnitude of this interaction, which includes both dipolar coupling and any contribution due to a small s-like component of the hole's Bloch wavefunction, may be estimated as 2 MHz from the results of muon spin resonance experiments [17]. Since the BE Zéeman energy is comparable to that of the bound electron, the probability of a spin flip due to the BE hyperfine coupling is smaller by the approximate factor $(2\ \mathrm{MHz}/60\ \mathrm{MHz})^2 \sim 10^{-3}$. Nuclear spin flip due to the P^0 hyperfine coupling during radiative decay has a similar order to that during free electron capture, but since radiative decay is 7000 times less frequent, this probability may also be neglected.

It is unfortunate that the predominant decay mechanism is non-radiative, since each Auger process increases the probability of nuclear randomization without providing a signal photon. After 2×10^6 excitations, at which point the probability of nuclear randomization exceeds 1/10, we can only expect to have collected and detected 25 photons or 5×10^3 photons with a DBR planar cavity or a 2D photonic crystal, respectively. This still yields a usable signal-to-noise ratio of 2 or 400 for the respective geometries. Thus, we expect the measurement-induced lifetime of the single nuclear spin to be long enough to allow for the measurement of the nuclear spin state.

In summary, we have proposed utilizing the sharp BE PL lines for single nuclear spin measurement. We have demonstrated that it is theoretically possible to measure a single donor impurity spin in silicon using currently available technology – a semiconductor microcavity and single-photon detectors. We have analyzed only one type of BE in Si, due to the experimentally observed strong hyperfine coupling and narrow PL linewidths. However, bound excitons exist in abundance in most semiconductors. Thus, this technique could be applied to many more systems if the crystal quality is sufficiently high and the hyperfine coupling and photon flux are sufficiently large. We believe this technique holds promise for state readout in quantum computers utilizing nuclear qubits in semiconductors.

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